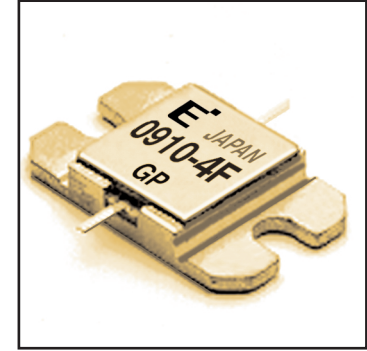


### FEATURES

- High Output Power:  $P_{1dB} = 36.0\text{dBm}$  (Typ.)
- High Gain:  $G_{1dB} = 7.5\text{dB}$  (Typ.)
- High PAE:  $\eta_{add} = 29\%$  (Typ.)
- Low  $IM_3 = -46\text{dBc}$  @  $P_o = 25.5\text{dBm}$
- Broad Band: 9.5 ~ 10.5GHz
- Impedance Matched  $Z_{in}/Z_{out} = 50\Omega$



### DESCRIPTION

The FLM0910-4F is a power GaAs FET that is internally matched for standard communication bands to provide optimum power and gain in a 50 ohm system.

Eudyna's stringent Quality Assurance Program assures the highest reliability and consistent performance.

### ABSOLUTE MAXIMUM RATING (Ambient Temperature $T_a=25^\circ\text{C}$ )

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	$V_{DS}$		15	V
Gate-Source Voltage	$V_{GS}$		-5	V
Total Power Dissipation	$P_T$	$T_C = 25^\circ\text{C}$	25.0	W
Storage Temperature	$T_{stg}$		-65 to +175	$^\circ\text{C}$
Channel Temperature	$T_{ch}$		175	$^\circ\text{C}$

Fujitsu recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain-source operating voltage ( $V_{DS}$ ) should not exceed 10 volts.
2. The forward and reverse gate currents should not exceed 16.0 and -2.2 mA respectively with gate resistance of  $100\Omega$ .

### ELECTRICAL CHARACTERISTICS (Ambient Temperature $T_a=25^\circ\text{C}$ )

Item	Symbol	Test Conditions	Limit			Unit
			Min.	Typ.	Max.	
Saturated Drain Current	$I_{DSS}$	$V_{DS} = 5V, V_{GS} = 0V$	-	1700	2600	mA
Transconductance	$g_m$	$V_{DS} = 5V, I_{DS} = 1100\text{mA}$	-	1700	-	mS
Pinch-off Voltage	$V_p$	$V_{DS} = 5V, I_{DS} = 85\text{mA}$	-0.5	-1.5	-3.0	V
Gate Source Breakdown Voltage	$V_{GSO}$	$I_{GS} = -85\mu\text{A}$	-5.0	-	-	V
Output Power at 1dB G.C.P.	$P_{1dB}$	$V_{DS} = 10V,$ $I_{DS} = 0.65 I_{DSS}$ (Typ.), $f = 9.5 \sim 10.5 \text{GHz},$ $Z_S = Z_L = 50 \text{ohm}$	35.5	36.0	-	dBm
Power Gain at 1dB G.C.P.	$G_{1dB}$		6.5	7.5	-	dB
Drain Current	$I_{dsr}$		-	1100	1300	mA
Power-added Efficiency	$\eta_{add}$		-	29	-	%
Gain Flatness	$\Delta G$		-	-	$\pm 0.6$	dB
3rd Order Intermodulation Distortion	$IM_3$	$f = 10.5 \text{GHz}, \Delta f = 10 \text{MHz}$ 2-Tone Test $P_{out} = 25.5\text{dBm S.C.L.}$	-44	-46	-	dBc
Thermal Resistance	$R_{th}$	Channel to Case	-	5.0	6.0	$^\circ\text{C/W}$
Channel Temperature Rise	$\Delta T_{ch}$	$10V \times I_{dsr} \times R_{th}$	-	-	80	$^\circ\text{C}$

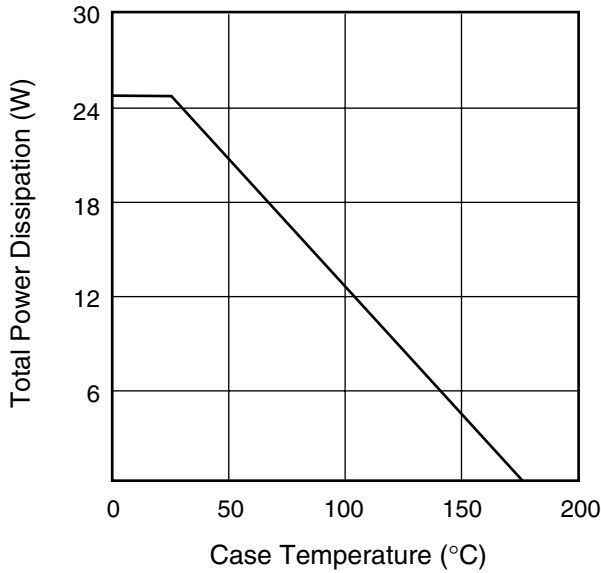
CASE STYLE: IA

G.C.P.: Gain Compression Point, S.C.L.: Single Carrier Level

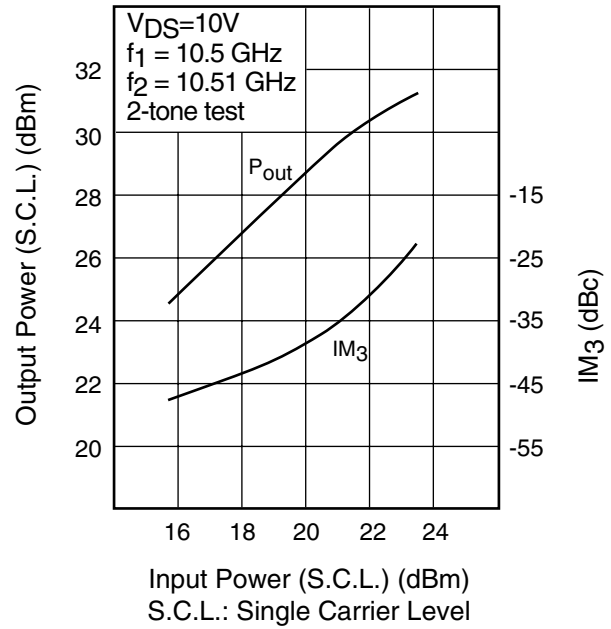
# FLM0910-4F

X, Ku-Band Internally Matched FET

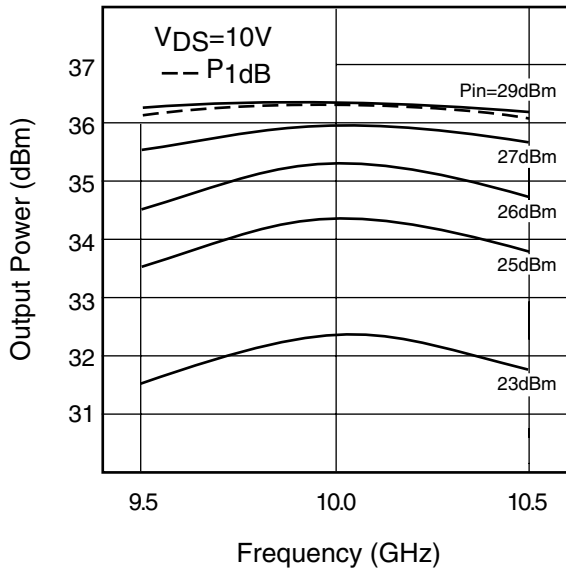
**POWER DERATING CURVE**



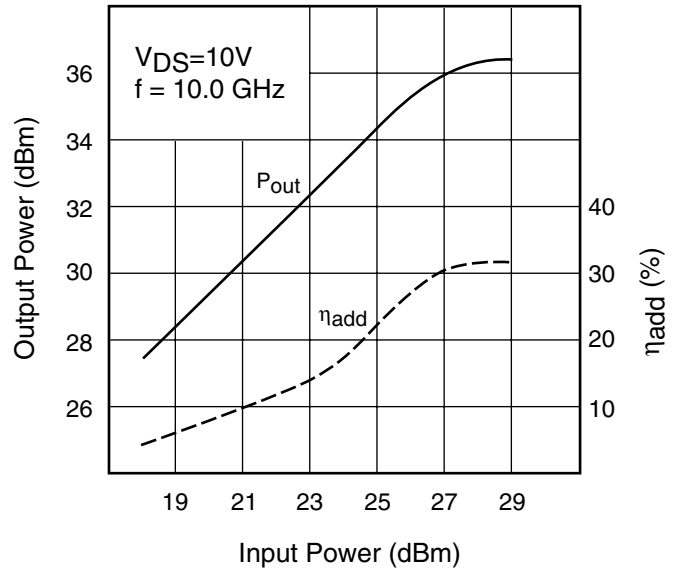
**OUTPUT POWER & IM<sub>3</sub> vs. INPUT POWER**



**OUTPUT POWER vs. FREQUENCY**

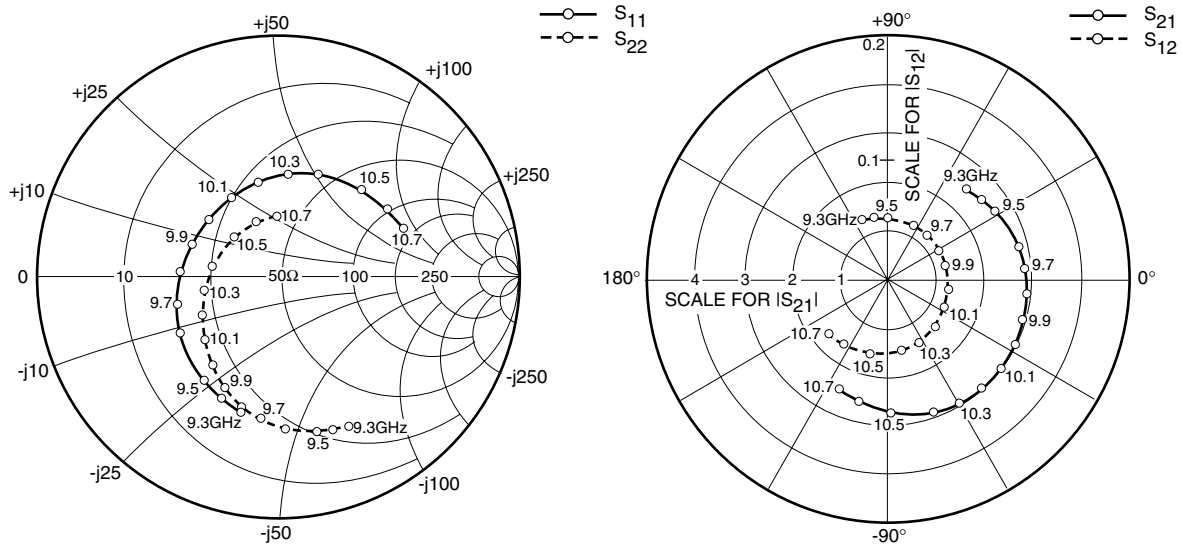


**OUTPUT POWER vs. INPUT POWER**



# FLM0910-4F

X, Ku-Band Internally Matched FET



## S-PARAMETERS

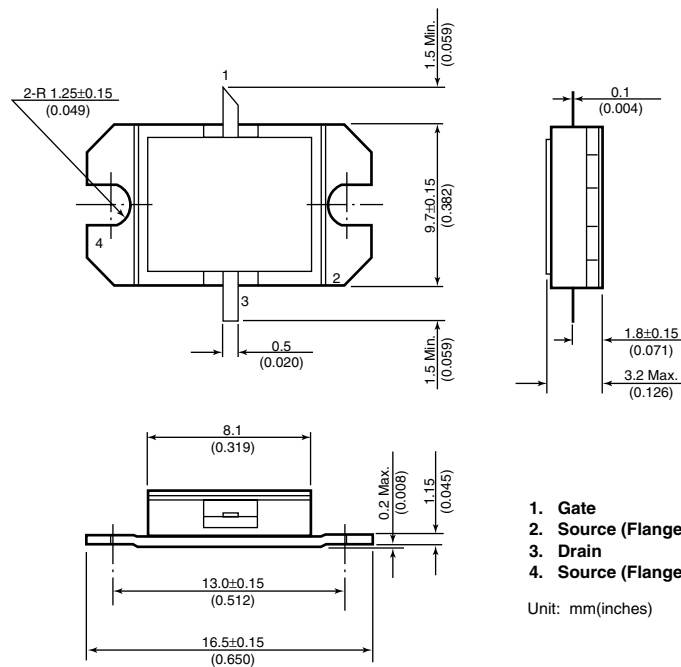
$V_{DS} = 10V, I_{DS} = 1100mA$

FREQUENCY (MHZ)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
9300	.585	-106.3	2.447	48.4	.053	113.7	.686	-65.4
9400	.559	-115.3	2.515	40.1	.053	103.2	.677	-70.8
9500	.530	-125.8	2.585	31.9	.051	90.5	.666	-76.4
9600	.467	-150.3	2.763	13.9	.049	62.4	.625	-89.7
9700	.435	-165.5	2.841	4.0	.049	47.4	.596	-97.3
9800	.410	177.6	2.906	-6.5	.046	28.0	.557	-106.1
9900	.385	159.3	2.934	-17.0	.049	13.1	.515	-115.8
10000	.378	140.6	2.946	-27.6	.051	-7.5	.463	-126.6
10100	.381	121.2	2.956	-38.1	.052	-27.6	.409	-139.1
10200	.402	102.4	2.964	-48.9	.053	-45.8	.356	-153.1
10300	.427	85.0	2.943	-59.8	.057	-61.5	.313	-169.5
10400	.456	69.1	2.898	-71.0	.059	-79.3	.277	171.6
10500	.499	46.8	2.742	-89.2	.064	-104.5	.246	138.5
10600	.532	31.7	2.590	-103.3	.065	-124.2	.243	111.8
10700	.553	21.2	2.448	-114.0	.067	-137.7	.251	91.3

# FLM0910-4F

## X, Ku-Band Internally Matched FET

### Case Style "IA" Metal-Ceramic Hermetic Package



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#### CAUTION

Eudyna Devices Inc. products contain **gallium arsenide (GaAs)** which can be hazardous to the human body and the environment. For safety, observe the following procedures:

- Do not put this product into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.

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